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_				Application Number	T.B.A.		
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9	STATEMENT BY APPLICANT			First Named Inventor	Wolfgang M.J. Hofmann		
				Group Art Unit	1772		
	(use as mai	ny sheets a	s necessary)	Examiner Name			
Sh	eet 1	of	1	Attorney Docket Number	Hofmann		

				U.S. PATENT DOC	UMENTS	70
Examiner Initials	Cite No.1	U.S. Patent I	Cocument Kind Code ² (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Cotumns, Lines, Where Relevant Passages or Relevant Figures Appear
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DUD		5,235,187		Arney	08/10/1993	
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	ute for form 1449A/PTO			Complete if Known		
	•			Application Number	T.,B.A.	
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ST	ATEMENT B	Y	APPLICANT	First Named Inventor	Wolfgang M.J. Hofmann	
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	(use as many shee	ets a	s necessary)	Examiner Name		
Sheet	1	of	1	Attorney Docket Number	Hofmann	

				U.S. PATENT DOCL	MENTS	
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WP		5,847,454		Shaw	12/08/1998	
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				FORE	IGN PATENT DOCUMENT	rs		
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Examiner Initials*	Cite No.1	Office ³	Number ⁴	Kind Code ⁵ (<i>if known</i>)	Applicant of Cited Document	Cited Document MM-DD-YYYY	Passages or Relevant Figures Appear	T6
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		Application Number	T.B.A.	
		Filing Date	Even Date Herewith	
		First Named Inventor	Wolfgang M.J. Hofmann	
		Group Art Unit	1772	
	(use as many sheets as necessary)	Examiner Name		
Sheet	1 of 6	Attorney Docket Number	Hofmann	

		OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the Item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-Issue number(s), publisher, city and/or country where published.	Τ2
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PUD		XU, Y., MacDonald, N.C., Miller, S.A.; Integrated Micro-scanning tunneling microscope; Applied Physics Letters, vol. 67, pp. 2305-7, 16 Oct. 1995.	
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		First Named Inventor	Wolfgang M.J. Hofmann	
		Group Art Unit	1772	
	(use as many sheets as necessary)	Examiner Name		
Sheet	1 01 6	Attorney Docket Number	Hofmann	

		OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the	
Examiner Initials	Cite No.1	include name of the author (in CAPITAL LETTERS), title of the altest (when appropriate), due of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²
N	1	MACDONALD, N.C.; SCREAM Microelectromechanical systems; Microelectronic Engineering, vol. 32, pp. 49-73, Sept. 1996	
W		JAZAIRY, A., MacDonald, N.C.; Planar very high aspect ratio microstructures for large loading forces; Microelectronic Engineering, vol. 30, pp. 527-30, Jan. 1996	
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M		CHANG, T.H.P.k Kern, D.P., Muray, L.P.; Microminiaturization of electron optical systems; J. Vacuum Science & Technology B, vol. 8, pp. 1698-1705, 1990	
M		CHANG, T.H.P., Kern, D.P., McCord, M.A., Muray, L.P.; A Scanning Tunneling Microscope Controlled Field Emission Microprobe System; J. Vacuum Science & Technology, vol. 9, pp. 438-443, 1991	
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